TOSHIBA HIGH SPEED THYRISTOR SILICON PLANAR TYPE

SH0R3D42

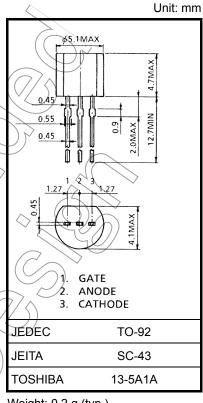
HIGH SPEED SWITCHING AND CONTROL APPLICATIONS

Repetitive Peak Off-State Voltage : VDRM = 200V
 Average On-State Current : IT (AV) = 300mA

• Plastic Mold Type.

ABSOLUTE MAXIMUM RATINGS

CHARACTERISTIC	SYMBOL	RATING	UNIT
Repetitive Peak Off–State Voltage ($R_{GK} = 1k\Omega$)	V _{DRM}	200	(\sqrt{y})
Non-Repetitive Peak Off-State Voltage ($R_{GK} = 1k\Omega$)	V _{DSM}	250))>/
Average On-State Current (Half Sine Waveform Ta = 30°C)	I _{T (AV)}	300	> mA
R.M.S On-State Current	I _{T (RMS)}	450	mA
Peak One Cycle Surge On-State Current (Non-Repetitive)	I _{TSM}	7 (50Hz)	A
I ² t Limit Value	I ² t	0.3	A^2 s
Peak Gate Power Dissipation	P _{GM}	0.1	w/
Average Gate Power Dissipation	PG (AV)	0.01	\ W
Peak Forward Gate Voltage	(V _{FGM})	3.5	\/v
Peak Reverse Gate Voltage	VRGM	-7	\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\
Peak Forward Gate Current	//)I _{GM}	125	MA
Junction Temperature	\mathcal{T}_{j}	-40~125	°C
Storage Temperature Range	T _{stg}	-40~125	°C

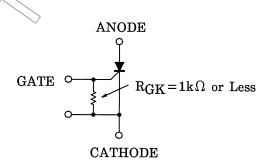


Weight: 0.2 g (typ.)

Note 1: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 2: Should be used with gate resistance as follows.



MARK

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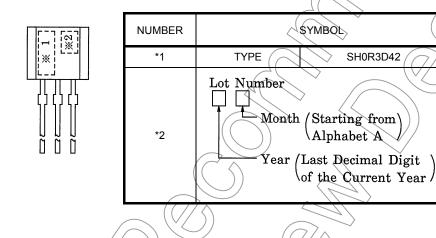
Example 8A : January 1998 8B : February 1998 8L : December 1998

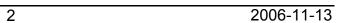
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

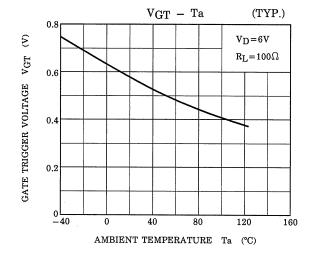
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN	MAX	UNIT
Repetitive Peak Off-State Current and Peak Reverse Current	I _{DRM}	T_j = 125°C, V_{DRM} = Rated R_{GK} = 1kΩ	_	100	μΑ
Peak On-State Voltage	V _{TM}	I _{TM} = 2A		1.8	V
Gate Trigger Voltage	V_{GT}	$V_D = 6V, R_L = 100\Omega$	_	0.9	٧
Gate Trigger Current	I _{GT}	VD = 0V, NL = 10002	7	1.0	mA
Gate Non-Trigger Voltage	$V_{\sf GD}$	V _D = Rated, Tc = 110°C	0.3	1	V
Turn-On Time	t _{gt}	V _D = Rated, I _{TM} = 4A I _G = 10mA	_	2.0	μs
Turn-Off Time	tq	$V_D = 20V, I_P = 1A, R_{GK} = 1k\Omega$	_	6.0	μs
Critical Rate of Rise of Off-State Voltage	dv / dt	V _D = Rated, R _{GK} = 1kΩ Tc = 110°C, Exponential Rise	15	ı	V / µs
Holding Current	lн	$R_L = 100\Omega, R_{GK} = 1 k\Omega$	4	15	mA
Thermal Resistance	R _{th (j-c)}	Junction to Ambient		250	°C/W

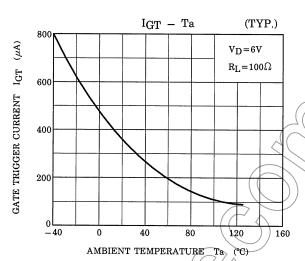
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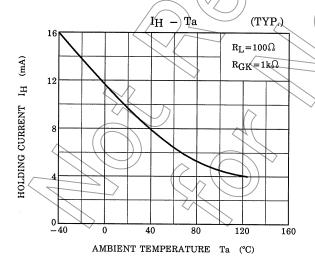
MARKING

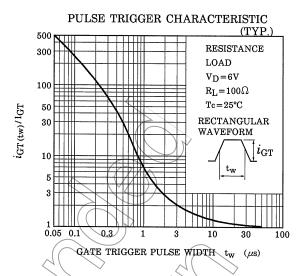


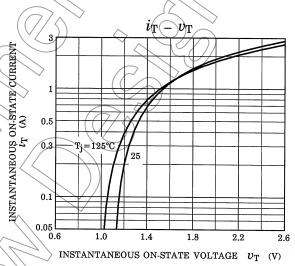












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